TOSHIBA INSULATED GATE BIPOLAR TRANSISTOR SILICON N - CHANNEL MOS TYPE

GT80J101

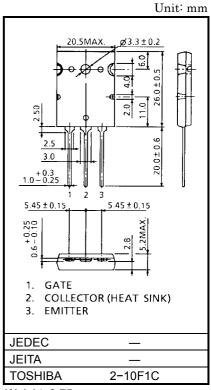
HIGH POWER SWITCHING APPLICATIONS

- High Input Impedance
 - High Speed : $t_f = 0.40 \mu s$ (Max.)
- Low Saturation Voltage : VCE (sat) = 3.5V (Max.)
- Enhancement-Mode

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MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT	
Collector-Emitter Voltage		V _{CES}	600	V	
Gate-Emitter Voltage		V _{GES}	±20	V	
Collector Current	DC	ΙC	80	А	
	1ms	I _{CP}	160		
Collector Power Dissipation (Tc = 25°C)		P _C	200	W	
Junction Temperature		Tj	150	°C	
Storage Temperature Range		T _{stg}	T _{stg} -55~150		
Screw Torque		—	0.8	N∙m	

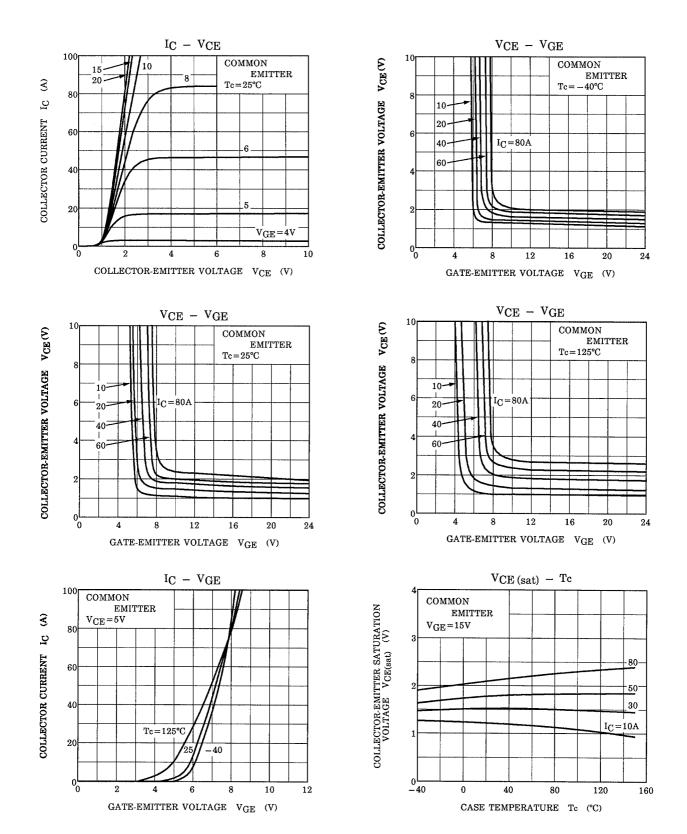


Weight: 9.75g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT	
Gate Leakage Current		I _{GES}	$V_{GE} = \pm 20V, V_{CE} = 0$	_	_	±500	nA	
Collector Cut-Off C	urrent	ICES	V _{CE} = 600V, V _{GE} = 0	—	—	1.0	mA	
Gate-Emitter Cut-c	off Voltage	V _{GE (OFF)}	I _C = 80mA, V _{CE} = 5V	3.0	—	6.0	V	
Collector-Emitter Saturation Voltage		V _{CE (sat) (1)}	I _C = 10A, V _{GE} = 15V	_	_	2.0	V	
		V _{CE (sat) (2)}	I _C = 80A, V _{GE} = 15V	_	2.5	3.5	v	
Input Capacitance		Cies	V _{CE} = 10V, V _{GE} = 0, f = 1MHz	_	5500	—	pF	
Switching Time	Rise Time	tr	$15V_{0} V_{IN_{0}} 33\Omega_{0} $	_	0.3	0.6	- µs	
	Turn-on Time	t _{on}		_	0.5	0.8		
	Fall Time	t _f		_	0.25	0.40		
	Turn-off Time	t _{off}		_	0.7	1.0		
Thermal Resistance		R _{th (j−c)}	—	_	—	0.625	°C/W	

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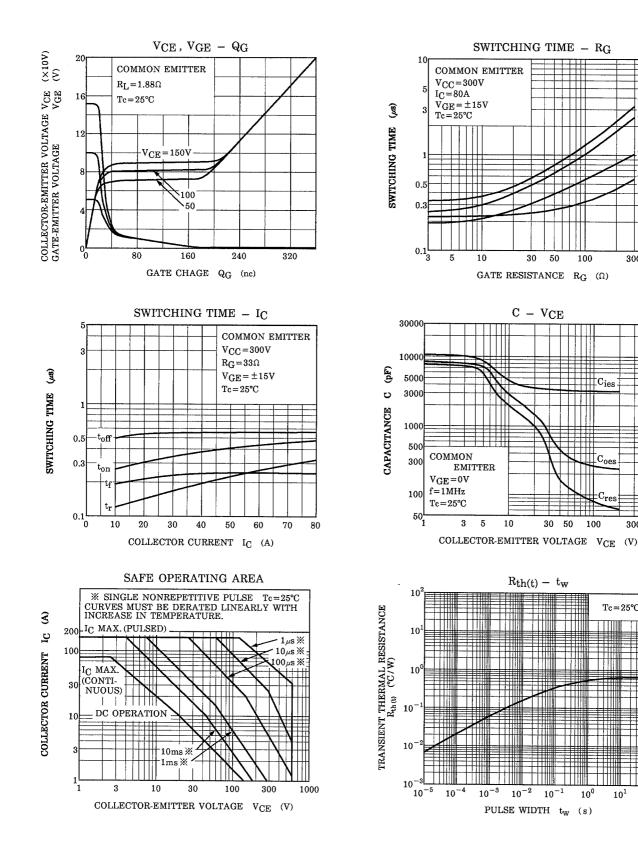
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300 500

 $Tc = 25^{\circ}C$

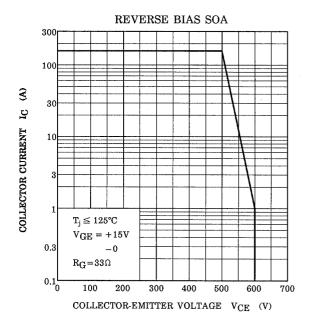
10¹

 10^2



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